

MIG10065A

650V Silicon Carbide Schottky Diode

DESCRIPTION :

- Negligible reverse recovery
- High Surge Currenr
- Positive temperature Coefficient
- High frequency
- RoHS Compliant

TYPICAL APPLICATIONS :

- Uninterruptible power supplies (UPS)
- Data Center
- Switch mode power supplies (SMPS)
- Solar inverter

V _{RRM}	650V		
١ _F	10A (TC=154°C)		
Qc	30nC		



TO-220AC

MAXIMUM RATINGS (at T_C = 25 °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V _{RRM}	650	V
Continuous Forward Current	Tc=25℃ Tc=135℃ Tc=154℃	I _F	32 15 10	A
Non-Repetitive Forward Surge Current	Tc=25°C , t_P=10ms, Half sine pulse Tc=110°C , t_P=10ms, Half sine pulse	I _{FSM}	96 83	А
Repetitive Peak Forward Surge Current	Tc=25 $^\circ\!\!\mathbb{C}$, tp=10ms, Half sine pulse	I _{FRM}	85	А
i ² t value	Tc=25℃ , t _P =10ms Tc=110℃ , t _P =10ms	∫ i ² dt	60.5 44	A ² S
Power dissipation	Tc=25℃ Tc=110℃ Tc=150℃	P _{tot}	127 55 21	w
Operation Junction temperature		Tj	-55~+175	°C
Storage temperature		T _{STG}	-55~+175	°C

MIG10065A

THERMAL CHARACTERISTICSCharacteristicConditionSymbolTypicalUnitThermal resistance,
junction - caseRth(j-C)1.175°C/W

ELECTRICAL CHARATERISTICS (at $T_c = 25$ °C, unless otherwise specified)

Characteristic	Symbol	Min.	Тур.	Max.	Unit
DC Blocking Voltage	V _{DC}	650			V
Forward Voltage IF = 5A IF = 10A, Tc =25°C IF = 10A, Tc =175°C	V _F		1.17 1.37 1.66	1.6	V
Reverse Current VR = 650V, Tc =25℃ VR = 650V, Tc =175℃	I _R		5 12	60	uA
Total Capacitive Charge VR = 400V	Q _c		30		nC
Total capacitance VR = 1V, f =1MHz VR = 200V, f =1MHz VR = 400V, f =1MHz	С		455 57 56		pF
Capacitance Stored Energy VR = 400 V	Ec		4.8		uJ

MIG10065A

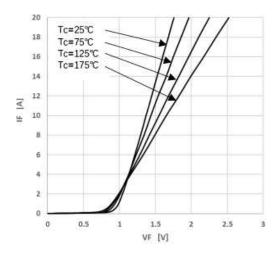


Figure 1. Forward characteristics

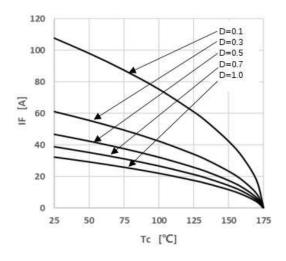


Figure 3. Peak Forward Current Derating

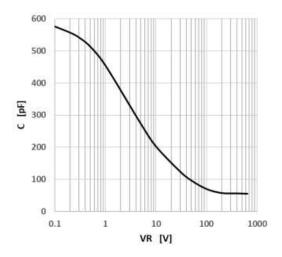


Figure 5. Capacitance vs. Reverse Voltage

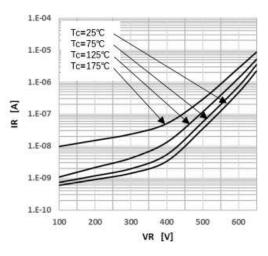


Figure 2. Reverse characteristics

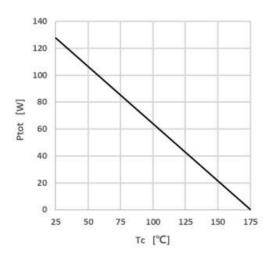


Figure 4. Power Dissipation

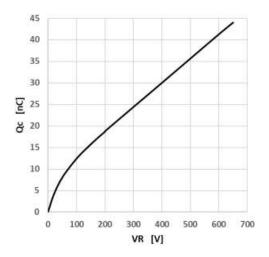


Figure 6. Capacitance Charge vs. Reverse Voltage

MIG10065A

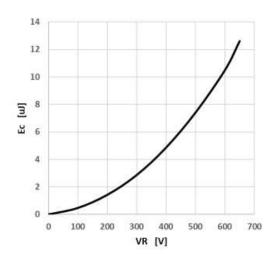


Figure 7. Capacitance Stored Energy

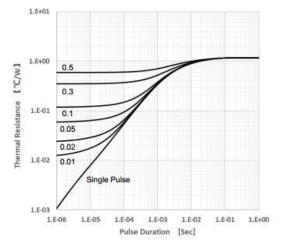
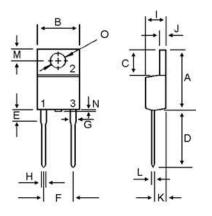


Figure 8. Transient Thermal Impedance

Circuit diagram



TO-220AC Package outlines : Dimensions in (mm)



DIM	MILLIMETERS		
ואוים	MIN	MAX	
Α	14.68	16.00	
В	9.78	10.42	
С	5.02	6.60	
D	13.00	14.62	
E	3.10	4.19	
F	4.82	5.34	
G	1.10	1.67	
Н	0.69	1.01	
I	4.22	4.98	
J	1.14	1.40	
K	2.20	3.30	
L	0.28	0.61	
М	2.48	3.00	
Ν		2.00	
0	3.50	4.00	



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